# The RF Line NPN Silicon High-Frequency Transistor

Tape and reel packaging available for MRF3866R2:
 R2 suffix = 2,500 units per reel

MRF3866R2

I<sub>C</sub> = 400 mA HIGH-FREQUENCY TRANSISTORS NPN SILICON

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	Vсво	55	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.5	Vdc
Collector Current — Continuous	IC	0.4	Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Maximum Junction Temperature	T <sub>Jmax</sub>	150	°C



CASE 751-05, STYLE 1 (SO-8)

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>0</sub> JC	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	125	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

,				
Characteristic	Symbol		Max	Unit
OFF CHARACTERISTICS	•			
Collector–Emitter Breakdown Voltage ( $I_C = 5.0 \text{ mAdc}, R_{BE} = 10 \Omega$ )	V(BR)CER	55	_	Vdc
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 5.0 mAdc, I <sub>B</sub> = 0)	VCEO(sus)	30	_	Vdc
Emitter–Base Breakdown Voltage ( $I_C = 100 \mu Adc$ , $I_C = 0$ )	V(BR)EBO	3.5	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 28 Vdc, I <sub>B</sub> = 0)	ICEO	_	0.02	mAdc
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}$ , $V_{BE} = -1.5 \text{ Vdc}$ (Rev.), $T_{C} = 150^{\circ}\text{C}$ ) ( $V_{CE} = 55 \text{ Vdc}$ , $V_{BE} = -1.5 \text{ Vdc}$ (Rev.)	ICEX	_ _	5.0 0.1	mAdc
Emitter Cutoff Current $(V_{BE} = 3.5 \text{ Vdc}, I_{C} = 0)$	IEBO	_	0.1	mAdc

(continued)



## **ELECTRICAL CHARACTERISTICS** — **continued** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit				
ON CHARACTERISTICS								
DC Current Gain (I <sub>C</sub> = 360 mAdc, $V_{CE}$ = 5.0 Vdc) (1) (I <sub>C</sub> = 50 mAdc, $V_{CE}$ = 5.0 Vdc)	hFE	5.0 10	 200	_				
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 20 mAdc)	VCE(sat)	_	1.0	Vdc				
SMALL-SIGNAL CHARACTERISTICS								
Current–Gain — Bandwidth Product (IC = 50 mAdc, $V_{CE}$ = 15 Vdc, f = 200 MHz)	f <sub>T</sub>	500	_	MHz				
Output Capacitance (V <sub>CB</sub> = 28 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	_	3.0	pF				
FUNCTIONAL TEST								
Amplifier Power Gain (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 1.0 W, f = 400 MHz)	G <sub>pe</sub>	10	_	dB				
Collector Efficiency (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 1.0 W, f = 400 MHz)	η	45	_	%				

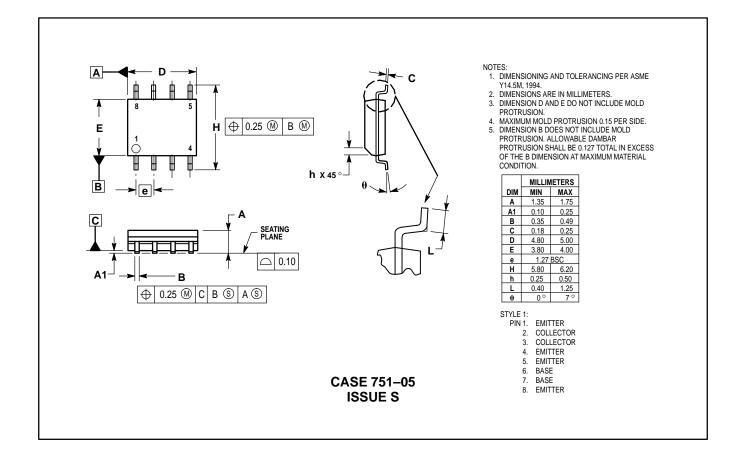
#### NOTE:

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%.$ 

VCE	lc	f	S <sub>11</sub>		s <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
(Volts)	(mA)	(MHz)	S <sub>11</sub>	∠ ф	S <sub>21</sub>	∠ ф	S <sub>12</sub>	∠ ф	S <sub>22</sub>	∠ ф
15	50	100	0.67	-166	13.75	92	0.016	44	0.32	-27
		200	0.69	-176	6.93	81	0.024	53	0.30	-24
		300	0.70	177	4.57	73	0.032	57	0.32	-31
		400	0.71	172	3.38	67	0.042	59	0.34	-37
		500	0.72	168	2.66	61	0.049	59	0.37	-45
		600	0.72	164	2.17	54	0.056	61	0.40	-53
		700	0.72	160	1.85	49	0.061	63	0.43	-60
		800	0.72	155	1.61	44	0.068	65	0.47	-66
		900	0.71	151	1.40	39	0.075	64	0.50	-73
		1000	0.70	146	1.25	34	0.084	68	0.53	-79

Table 1. MRF3866R2 Common Emitter S-Parameters

#### **PACKAGE DIMENSIONS**



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